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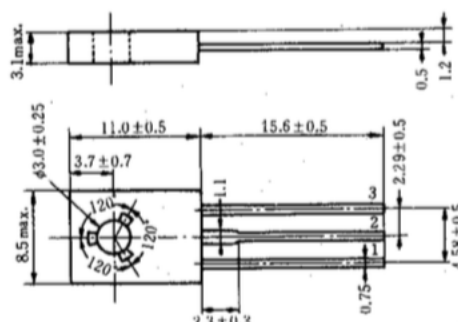
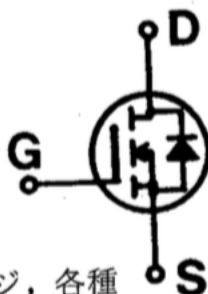
SILICON N-CHANNEL MOS FET

高速度電力スイッチング

高周波電力増幅

特長

- 高周波特性が優れている。
- 入出力容量が低い。
- 高精細ディスプレイのビデオ出力ステージ、各種用途のドライバ等に最適。



(Dimensions in mm)

(JEDEC TO-126 MOD.)

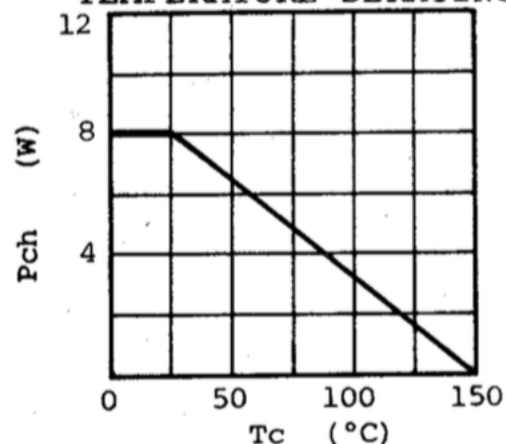
1. Source
2. Drain
3. Gate

■ ABSOLUTE MAXIMUM RATINGS (Ta=25°C)

Item	Symbol	Rating	Unit
Drain-Source Voltage	V _{DSS}	250	V
Gate-Source Voltage	V _{GS}	±9	V
Drain Current	I _D	0.3	A
Drain Peak Current	I _{D(peak)}	0.5	A
Body-Drain Diode Reverse Drain Current	I _{DR}	0.3	A
Channel Dissipation	P _{ch} *	8	W
Channel Temperature	T _{ch}	150	°C
Storage Temperature	T _{stg}	-55 ~ +150	°C

*Value at T_c=25°C

POWER VS. TEMPERATURE DERATING



■ ELECTRICAL CHARACTERISTICS (Ta=25°C)

Item	Symbol	Test Condition	min.	typ.	max.	Unit
Drain-Source Breakdown Voltage	V _{(BR)DSS}	I _D =1mA, V _{GS} =0	250	-	-	V
Gate-Source Leak Current	I _{GSS}	V _{GS} =±9 V, V _{DS} =0	-	-	±1	mA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =200V, V _{GS} =0	-	-	1	mA
Gate-Source Cutoff Voltage	V _{GS(off)}	I _D =1mA, V _{DS} =10V	1.0	-	5.0	V
Static Drain-Source On State Resistance	R _{DS(on)}	I _D =0.1A, V _{GS} =9V *	-	30	50	Ω
Drain-Source Saturation Voltage	V _{DS(on)}	I _D =0.1A, V _{GS} =9V *	-	3.0	5.0	V
Forward Transfer Admittance	y _{fs}	I _D =0.15A, V _{DS} =20V *	50	80	-	mS
Input Capacitance	C _{iss}	V _{DS} =10 V, V _{GS} =0	-	20	-	pF